N-Channel 80 V (D-S) Super Junction Power MOSFET

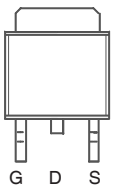
PRODUCT SUMMARY			
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)[c]	Q_g (Typ.)
80	0.0039 at V_{GS} = 10 V	120	83 nC
	0.0062 at V_{GS} = 4.5 V	70	

FEATURES

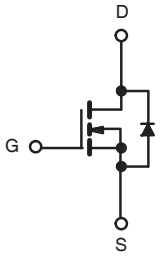
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

RoHS COMPLIANT

TO-252



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (T_J = 175 °C)[b]	T_C = 25 °C	I_D	120	A
	T_C = 100 °C		70[a]	
Pulsed Drain Current		I_{DM}	480	
Continuous Source Current (Diode Conduction)		I_S	120	
Avalanche Current		I_{AS}	115	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E_{AS}	258	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	351	W
	T_C = 125 °C		117	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	12	20	°C/W
	Steady State		21	35	
Maximum Junction-to-Case		R_{thJC}	0.78	1.0	

Notes:
a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t ≤ 10 s.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	80			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 64 V, V_{GS} = 0 V			1	µA
		V_{DS} = 64 V, V_{GS} = 0 V, T_J = 125 °C			10	
		V_{DS} = 64V, V_{GS} = 0 V, T_J = 175 °C			150	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 10 V, V_{GS} = 10 V	120			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 30A		0.0039	0.0047	Ω
		V_{GS} = 4.5 V, I_D = 20 A		0.0062	0.0077	
Forward Transconductance[b]	g_{fs}	V_{DS} = 64 V, I_D = 30 A		78		S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 40 V, f = 1 MHz		8865		pF
Output Capacitance	C_{oss}			2047		
Reverse Transfer Capacitance	C_{rss}			369		
Total Gate Charge[c]	Q_g	V_{DS} = 40 V, V_{GS} = 10 V, I_D = 20A		83	125	nC
Gate-Source Charge[c]	Q_{gs}			25		
Gate-Drain Charge[c]	Q_{gd}			30		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 40 V, R_L = 0.6 Ω I_D ≅ 30 A, V_{GEN} = 10 V, R_g = 2.5 Ω		12		ns
Rise Time[c]	t_r			21		
Turn-Off Delay Time[c]	$t_{d(off)}$			53		
Fall Time[c]	t_f			25		
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)						
Pulsed Current	I_{SM}				480	A
Diode Forward Voltage	V_{SD}	I_F = 20 A, V_{GS} = 0 V		0.8	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 30 A, di/dt = 100 A/µs		127		ns

Notes:

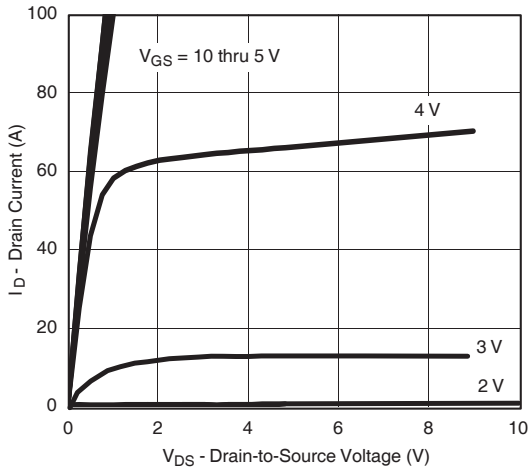
a. For design aid only; not subject to production testing.

b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

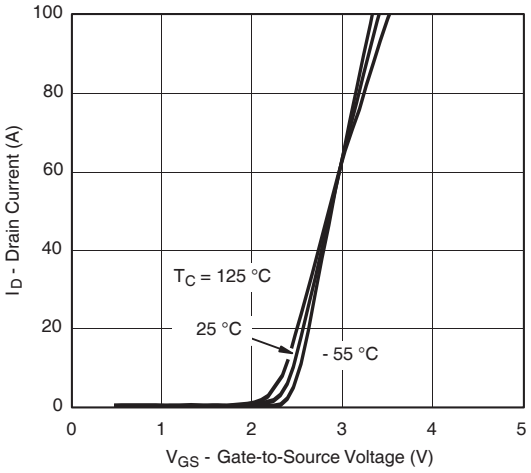
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

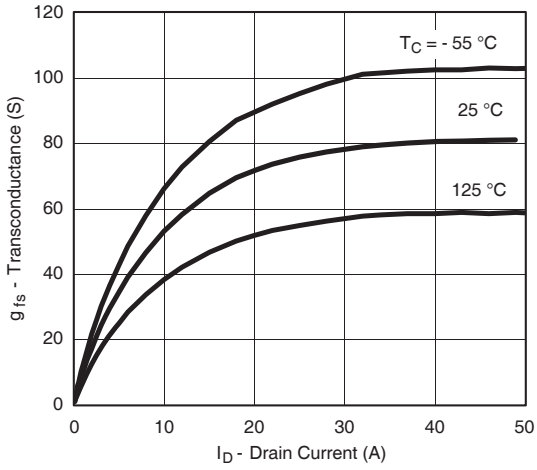
TYPICAL CHARACTERISTICS (25 °C unless noted)



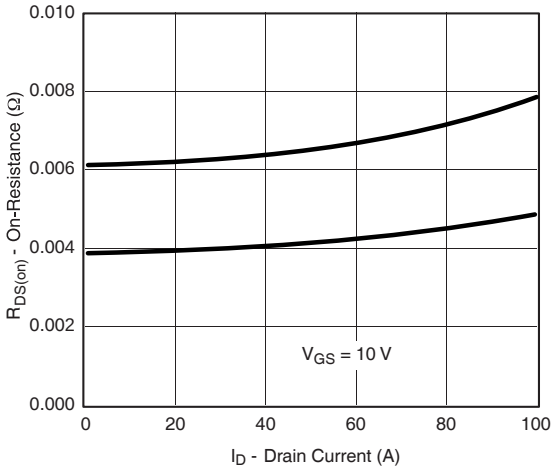
Output Characteristics



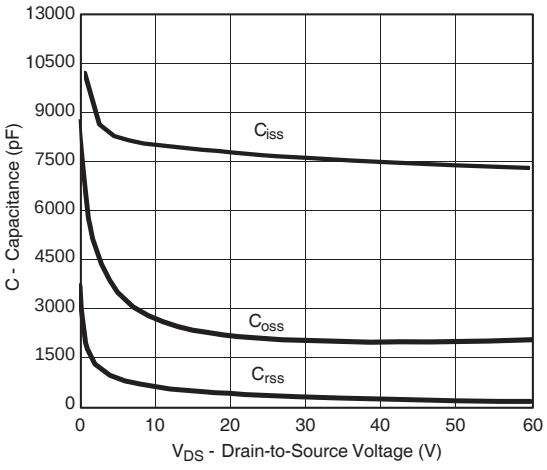
Transfer Characteristics



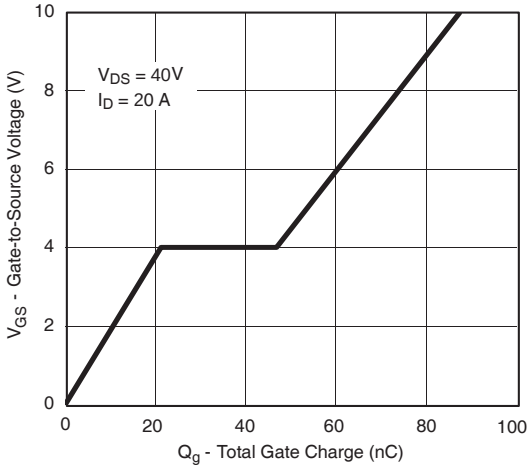
Transconductance



On-Resistance vs. Drain Current

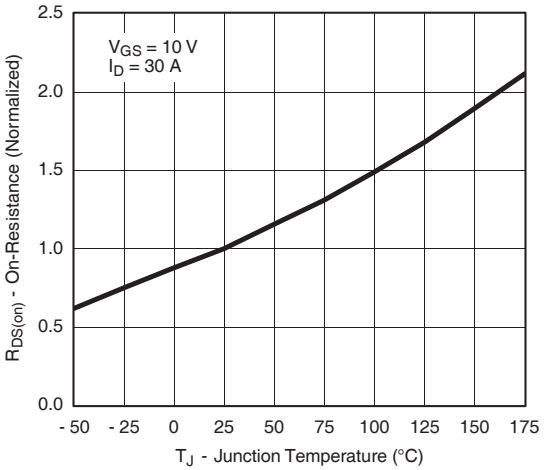


Capacitance

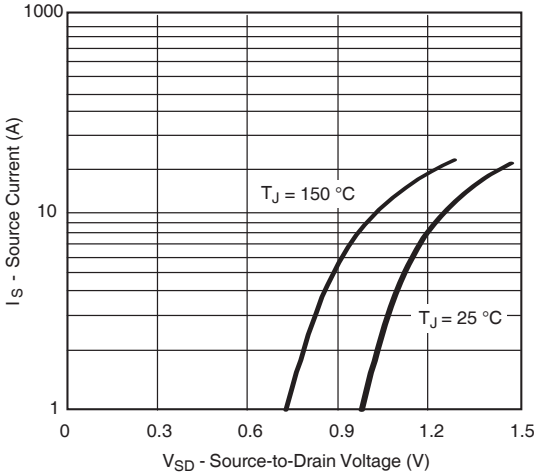


Gate Charge

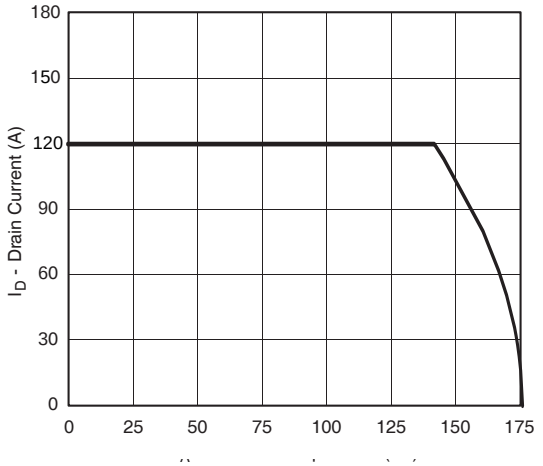
TYPICAL CHARACTERISTICS (25 °C unless noted)



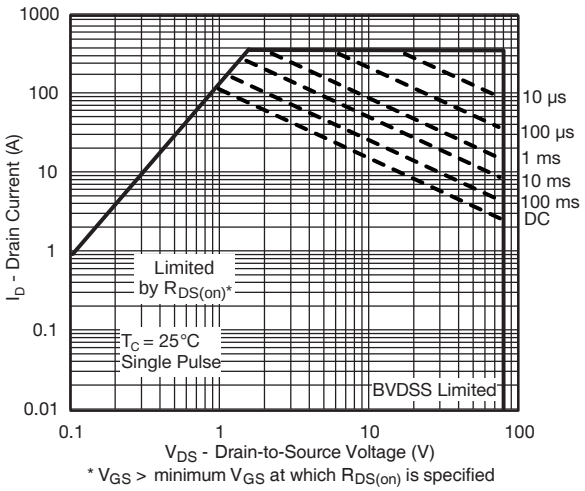
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

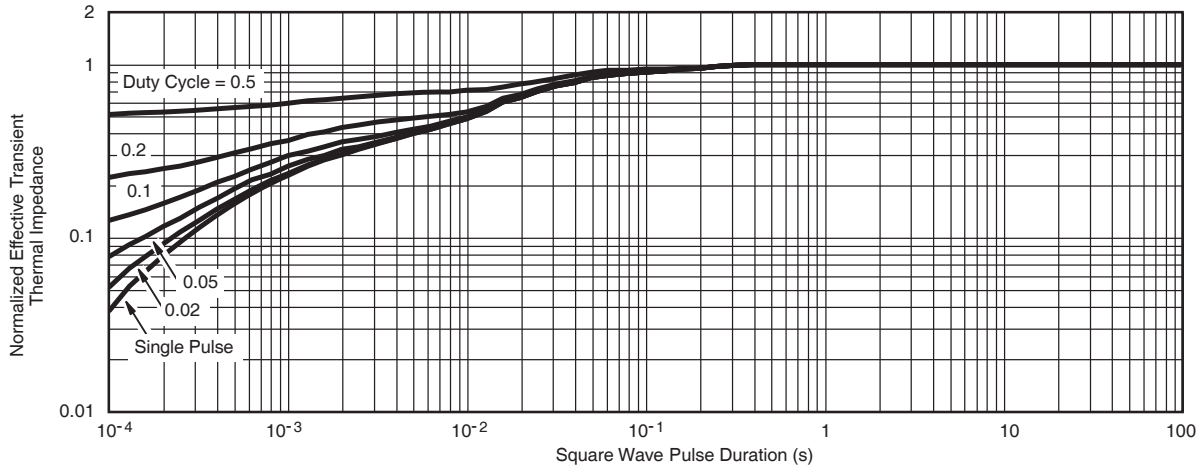


Maximum Drain Current vs. Ambient Temperature



Safe Operating Area

THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Din-Tek Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Din-Tek"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Din-Tek makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Din-Tek disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Din-Tek's knowledge of typical requirements that are often placed on Din-Tek products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Din-Tek's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Din-Tek products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Din-Tek product could result in personal injury or death. Customers using or selling Din-Tek products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Din-Tek personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Din-Tek. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Din-Tek documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Din-Tek documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.